



QL78D6S-A/B/C

AlGaAs Laser Diode

Ver.0 JAN 2004

◆ OVERVIEW

QL78D6S-A/B/C is a MOCVD grown 780nm band AlGaAs laser diode with quantum well structure.

It's an attractive light source, with a typical light output power of 5mW for industrial optical module and sensor applications.

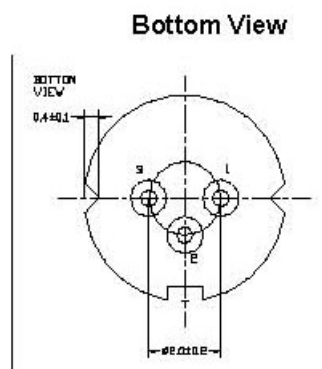
◆ APPLICATION

- CD-P

◆ FEATURES

- Lasing Wavelength : $\lambda_p = 780\text{nm}$
- Optical Power Output : 5mW CW
- Package Type : TO-18 (5.6mm Φ)
- Built-in Photo Diode for Monitoring Laser Output

◆ ELECTRICAL CONNECTION



Pin Configuration

A	LD cathode, PD anode (Fig. 1)
B	LD, PD anode (Fig. 2)
C	LD anode, PD cathode (Fig. 3)

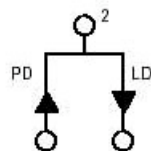


Fig. 1

QL78D6SA

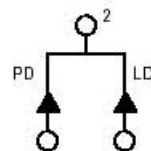


Fig. 2

QL78D6SB

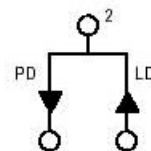


Fig. 3

QL78D6SC



◆ ABSOLUTE MAXIMUM RATING

Items	Symbols	Values	Unit
Optical Output Power	P	6	mW
Laser Diode Reverse Voltage	V	2	V
Photo Diode Reverse Voltage	V	30	V
Operating Temperature	T _{opr}	-10 ~ +60	°C
Storage Temperature	T _{stg}	-40 ~ +80	°C

◆ ELECTRICAL and OPTICAL CHARACTERISTICS

Items	Symbols	Min.	Typ.	Max.	Unit	Condition
Optical Output Power	P _o	-	5	-	mW	-
Threshold Current	I _{th}	-	20	30	mA	-
Operating Current	I _{op}	-	30	40	mA	P _o =5mW
Operating Voltage	V _{op}	-	1.9	2.3	V	P _o =5mW
Slope Efficiency	SE	0.3	0.5	0.7	mW/mA	P _o =3 ~ 5mW
Lasing Wavelength	λ _p	770	785	800	nm	P _o =5mW
Beam Divergence	θ	8	11	15	deg	P _o =5mW
	θ _⊥	25	34	40	deg	P _o =5mW
Beam Angle	Δθ	-	-	±1.5	deg	P _o =5mW
	Δθ _⊥	-	-	±2.5	deg	P _o =5mW
Monitor Current	I _m	0.1	0.3	0.6	mA	P _o =5mW
Optical Distance	ΔX, ΔY, ΔZ	-	-	±60	μm	P _o =5mW
Astigmatism	As	-	-	15	μm	P _o =5mW

NOTICE : QL78D6S-A/B/C to be operated on APC

The above product specifications are subject to change without notice.



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◆ PACKAGE DIMENSION

